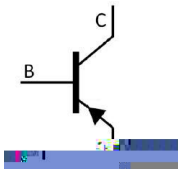


WR0<50 P M M E SQS æ M y s ll 1 Silicon PNP transistor in a TO-92LM Plastic Package.

Low $V_{CE(sat)}$, complements the 2SD1862.

Medium power amplifier applications.



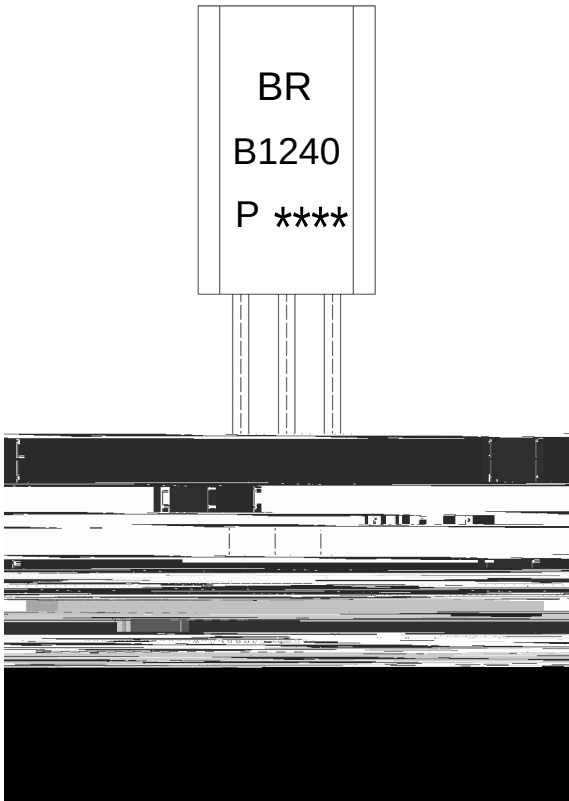
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

h _{FE} Classifications Symbol	P	Q	R
h _{FE} Range	82 180	120 270	180 390

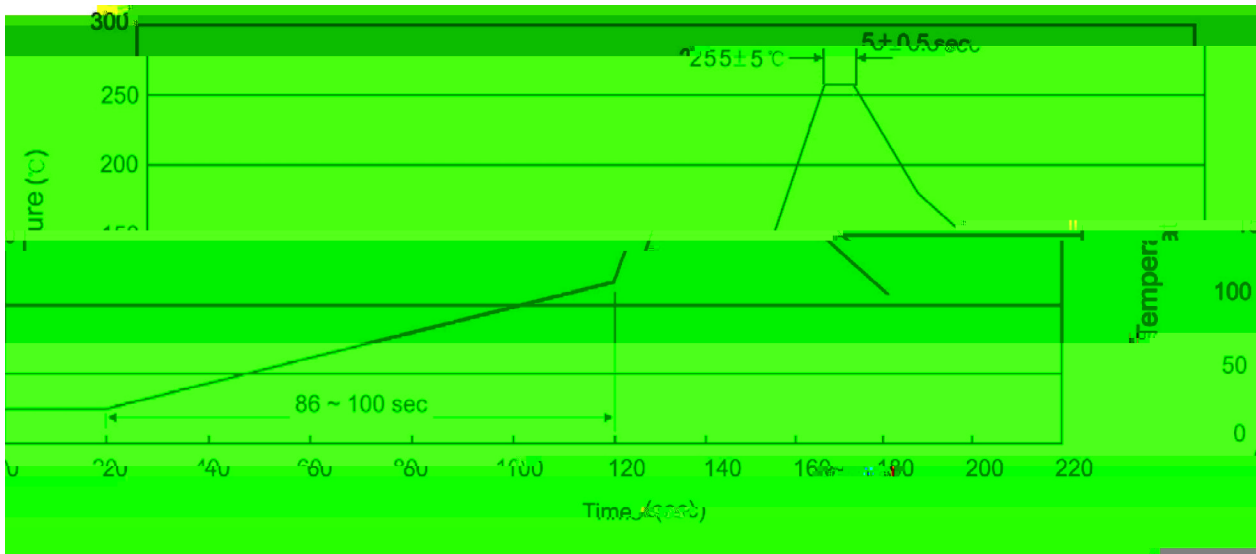
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-32	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current (DC)	I_C	-2.0	A
Collector Current-Peak	I_{CM}	-3.0	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -50\text{ A}$ $I_E = 0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0\text{ mA}$ $I_B = 0$	-32			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -50\text{ A}$ I_C				





公司代码	公司代码
EU:	公司代码
E4573	公司代码
S:	公司代码
----	公司代码 公司代码
Note:	
BR:	Company Code.
B1240:	Product Type.
P:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.



℃ ×

1. 预加热: 25~150℃, 时间: 60~90sec;
2. 峰值温度: 255±5℃, 持续时间: 5±0.5sec;
3. 冷却速度: 2~10℃/sec.

Note:

1. Preheating: 25~150℃, Time: 60~90sec.
2. Peak Temp.: 255±5℃, Duration: 5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

℃ × 270±5℃ 时间: 10±1 sec. Temp.: 270±5 Time: 10±1 sec

“Q” 符号 / BULK

Package Type	Units					Dimension (unit mm3)		
	Units/Bag	Bags/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Bag	Inner Box	Outer Box
TO-92LM	1,000	8	8,000	5	40,000	135×190	237×172×102	560×245×195

“V” 符号 / AMMO

Package Type	Units					Dimension (unit mm3)	
	Units/tape	Tape/Inner Box	Rows/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Inner Box	Outer Box
TO-92LM	2,500	1	100	10	25,000	328×230×42	